

P-Channel Power MOSFET

-20V, -2.8A, 130mΩ

Features

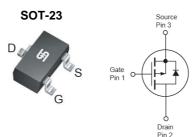
- Advance Trench Process Technology
- High Density Cell Design for Ultra Low Onresistance

| KEY PERFORMANCE PARAMETERS | | | | |
|----------------------------|------------------|-------|------|--|
| PARAMETER | | VALUE | UNIT | |
| V _{DS} | | -20 | V | |
| R _{DS(on)} (max) | $V_{GS} = -4.5V$ | 130 | | |
| | $V_{GS} = -2.5V$ | 190 | mΩ | |
| Qg | | 7.2 | nC | |



- Telecom power
- Consumer Electronics





Notes: Moisture sensitivity level: level 3. Per J-STD-020

| ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted) | | | | | |
|---|--|-----------------------------------|--------------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | | V _{DS} | -20 | V | |
| Gate-Source Voltage | | V _{GS} ±12 | | V | |
| Continuous Drain Current (Note 1) | T _C = 25°C | I _D | -2.8 | ٨ | |
| Continuous Drain Current | $T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 100^{\circ}{\rm C}$ | | -1.6 | A | |
| Pulsed Drain Current (Note 2) | | I _{DM} | -10 | А | |
| Continuous Source Current (Diode Conduction) (Note 3) | | I _S | -1 | А | |
| Tatal Dawar Diasis stian | $T_A = 25^{\circ}C$ | P | 0.7 | W | |
| Total Power Dissipation | $T_A = 70^{\circ}C$ | P _{DTOT} | 0.45 | | |
| Operating Junction and Storage Temperatur | e Range | T _J , T _{STG} | - 55 to +150 | °C | |

| THERMAL PERFORMANCE | | | | |
|--|------------------|-------|--------|--|
| PARAMETER | SYMBOL | LIMIT | Γ UNIT | |
| Junction to Ambient Thermal Resistance (PCB mounted) | R _{eja} | 175 | °C/W | |

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.



| ELECTRICAL SPECIFICATIONS (T _c = 25°C unless otherwise noted) | | | | | | |
|---|---|---------------------|------|------|------|------|
| PARAMETER | CONDITIONS | SYMBOL | MIN | ТҮР | МАХ | UNIT |
| Static (Note 4) | · | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = 250 \mu A$ | BV _{DSS} | -20 | | | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | V _{GS(th)} | -0.6 | -0.7 | -1 | V |
| Gate Body Leakage | $V_{GS} = \pm 12V, V_{DS} = 0V$ | I _{GSS} | | | ±100 | nA |
| Zero Gate Voltage Drain Current | $V_{DS} = -20V, V_{GS} = 0V$ | I _{DSS} | | | 1.0 | μA |
| Drain-Source On-State Resistance | $V_{GS} = -4.5V, I_{D} = -2.8A$ | R _{DS(on)} | | 90 | 130 | mΩ |
| | $V_{GS} = -2.5V, I_D = -2.0A$ | | | 120 | 190 | |
| Dynamic (Note 5) | · | | | | | |
| Gate Resistance | $V_{GS} = V_{DS} = 0V$, f=1MHz | R _g | | 7.5 | | Ω |
| Total Gate Charge | | Qg | | 7.2 | | |
| Gate-Source Charge | $V_{DS} = -6V, I_D = -2.8A,$ | Q _{gs} | | 2.2 | | nC |
| Gate-Drain Charge | $V_{GS} = -4.5V$ | Q _{gd} | | 1.2 | | |
| Input Capacitance | | C _{iss} | | 480 | | |
| Output Capacitance | $V_{DS} = -15V, V_{GS} = 0V,$ | C _{oss} | | 460 | | pF |
| Reverse Transfer Capacitance | f = 1.0MHz | C _{rss} | | 10 | | |
| Switching (Note 6) | | | | | | |
| Turn-On Delay Time | $V_{DD} = -6V, R_{L} = 6\Omega,$ $V_{GEN} = -4.5V,$ $R_{G} = 6\Omega$ | t _{d(on)} | | 38 | | |
| Turn-On Rise Time | | t _r | | 25 | | |
| Turn-Off Delay Time | | t _{d(off)} | | 43 | | ns |
| Turn-Off Fall Time | - KG - 012 | t _f | | 5 | | |
| Source-Drain Diode (Note 4) | | | | | | |
| Forward On Voltage | I_{S} = -1A, V_{GS} = 0V | V_{SD} | | -0.7 | -1.3 | V |
| | | | | | | |

Notes:

1. Current limited by package.

2. Pulse width limited by the maximum junction temperature.

3. Surface Mounted on a 1 in² pad of 2_{OZ} Cu, t ≤ 10 sec.

4. Pulse test: $PW \le 300\mu s$, duty cycle $\le 2\%$.

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



ORDERING INFORMATION

| PART NO. | PACKAGE | PACKING |
|----------------|---------|---------------------|
| TSM2301ACX RFG | SOT-23 | 3,000 pcs / 7" Reel |

Note:

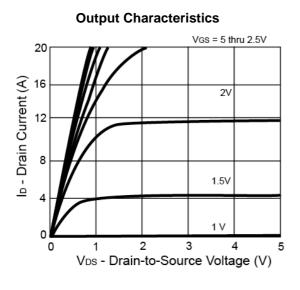
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

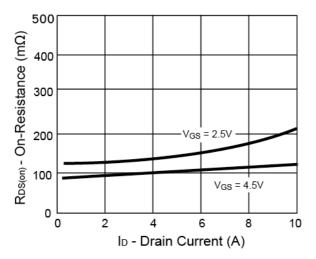


CHARACTERISTICS CURVES

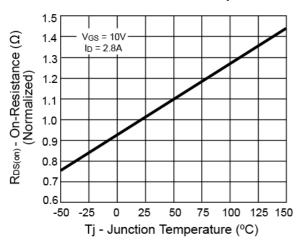
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$



On-Resistance vs. Drain Current

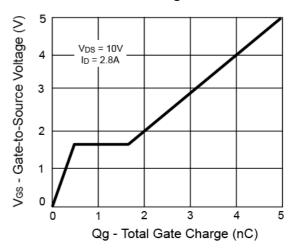


On-Resistance vs. Junction Temperature

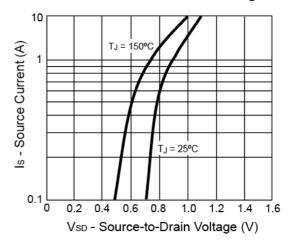


Transfer Characteristics 20 Tc = -55°C Ip - Drain Current (A) 16 25°C 12 125ºC 8 4 0 0 0.5 1.5 2.0 2.5 3.0 3.5 4.0 1.0 VGs - Gate-to-Source Voltage (V)

Gate Charge



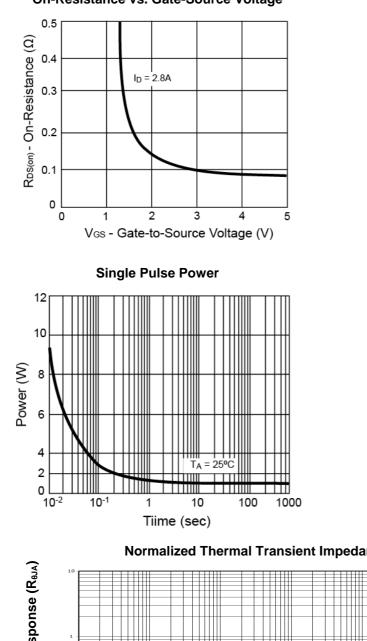
Source-Drain Diode Forward Voltage



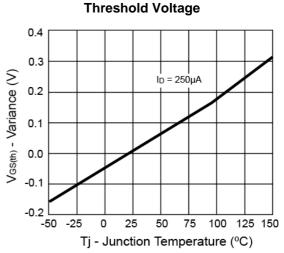


Electrical Characteristics Curve

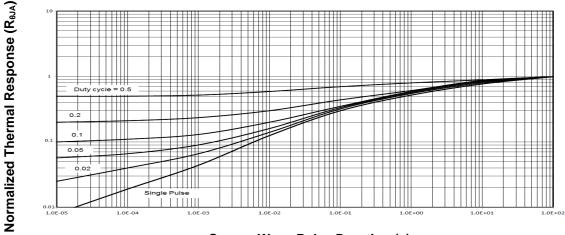
(Tc= 25°C, unless otherwise noted)



On-Resistance vs. Gate-Source Voltage



Normalized Thermal Transient Impedance, Junction-to-Ambient

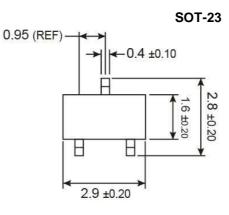


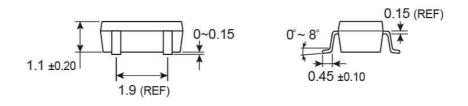
Square Wave Pulse Duration (s)



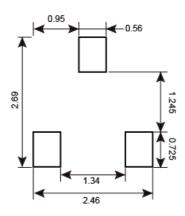


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

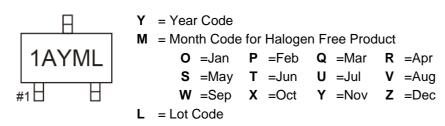




SUGGESTED PAD LAYOUT (Unit: Millimeters)



Marking Diagram





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